



# BUK9M31-60EL

Single N-channel 60 V, 21 mOhm logic level MOSFET in LFPAK33 using Enhanced SOA technology

7 April 2022

Product data sheet

## 1. General description

Single, logic level, N-channel MOSFET in LFPAK33 using Application specific (ASFET) Enhanced SOA technology. This product has been designed and qualified to AEC-Q101 for use in linear mode in airbag applications.

## 2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Enhanced SOA technology for improved linear mode performance
- LFPAK copper clip package technology:
  - High robustness and current handling capability
  - Gull wing leads for easy AOI inspection and exceptional board level reliability

## 3. Applications

- 12 V automotive systems
- Airbag squib voltage regulator MOSFET

## 4. Quick reference data

Table 1. Quick reference data

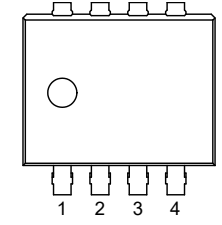
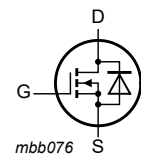
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		-	-	60	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ <a href="#">Fig. 2</a>	[1]	-	-	35	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ <a href="#">Fig. 1</a>		-	-	70.2	W
<b>Static characteristics</b>							
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 10\text{ A}; T_j = 25\text{ °C};$ <a href="#">Fig. 13</a>		11.6	16.5	20.6	mΩ
<b>Dynamic characteristics</b>							
$Q_{GD}$	gate-drain charge	$I_D = 10\text{ A}; V_{DS} = 48\text{ V}; V_{GS} = 5\text{ V};$ $T_j = 25\text{ °C};$ <a href="#">Fig. 15</a> ; <a href="#">Fig. 16</a>		-	6	11.9	nC

[1] 35 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFAK33 (SOT1210)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	Mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9M31-60EL	LFAK33	Plastic, single ended surface mounted package (LFAK33); 8 leads; 0.65 mm pitch	SOT1210

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9M31-60EL	9316EL

## 8. Limiting values

Table 5. Limiting values

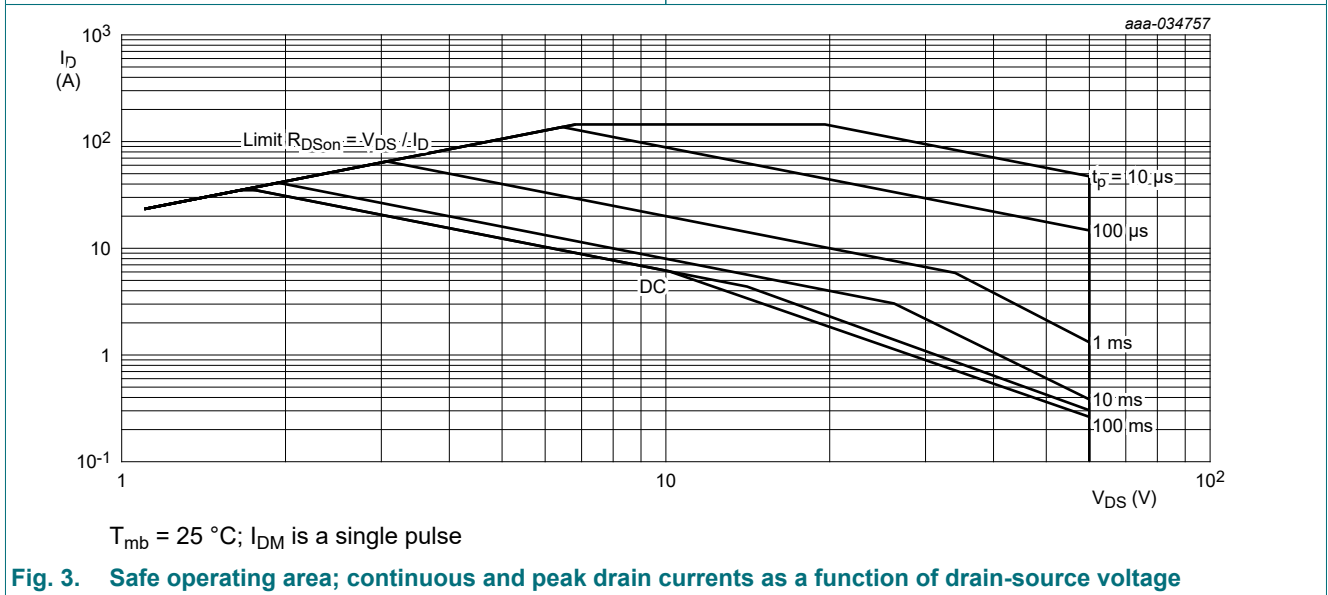
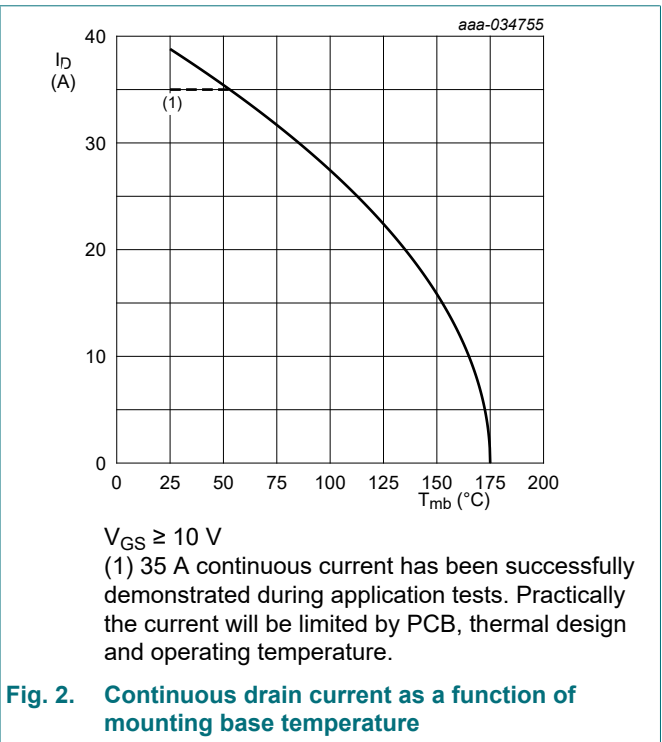
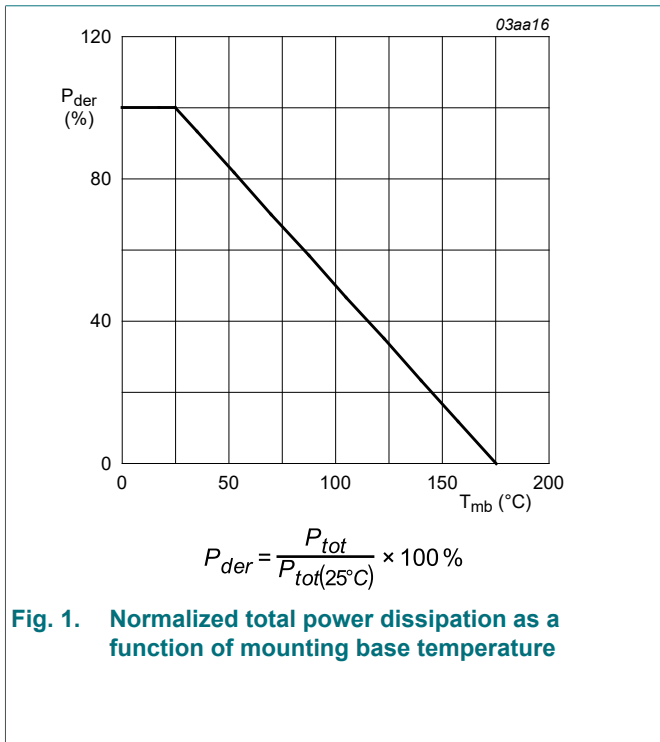
In accordance with the Absolute Maximum Rating System (IEC 60134).  $T_j = 25\text{ °C}$  unless otherwise stated.

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	60	V	
$V_{GS}$	gate-source voltage	$T_j = 175\text{ °C}$	-10	10	V	
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; Fig. 1	-	70.2	W	
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 2	[1]	-	35	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; Fig. 2		-	27	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 3; Fig. 4	-	155	A	
$T_{stg}$	storage temperature		-55	175	°C	
$T_j$	junction temperature		-55	175	°C	
$T_{sld(M)}$	peak soldering temperature		-	260	°C	
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	35	A	
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$	-	155	A	

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Symbol	Parameter	Conditions	Min	Max	Unit	
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 28.7 \text{ A}$ ; $V_{sup} \leq 60 \text{ V}$ ; $R_{GS} = 50 \text{ }\Omega$ ; $V_{GS} = 5 \text{ V}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; unclamped; $t_p = 36 \text{ }\mu\text{s}$ ; Fig. 5	[2] [3]	-	40.4	mJ
$I_{AS}$	non-repetitive avalanche current	$V_{sup} = 60 \text{ V}$ ; $V_{GS} = 5 \text{ V}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; $R_{GS} = 50 \text{ }\Omega$ ; Fig. 5	[2] [3]	-	28.7	A

- [1] 35 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.



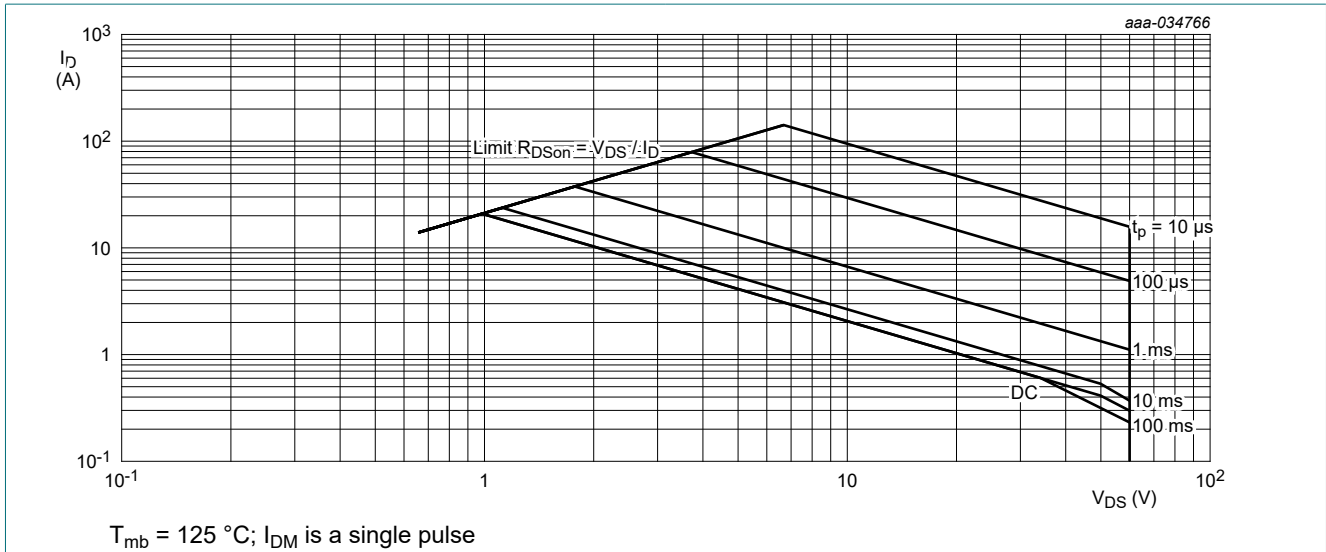


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

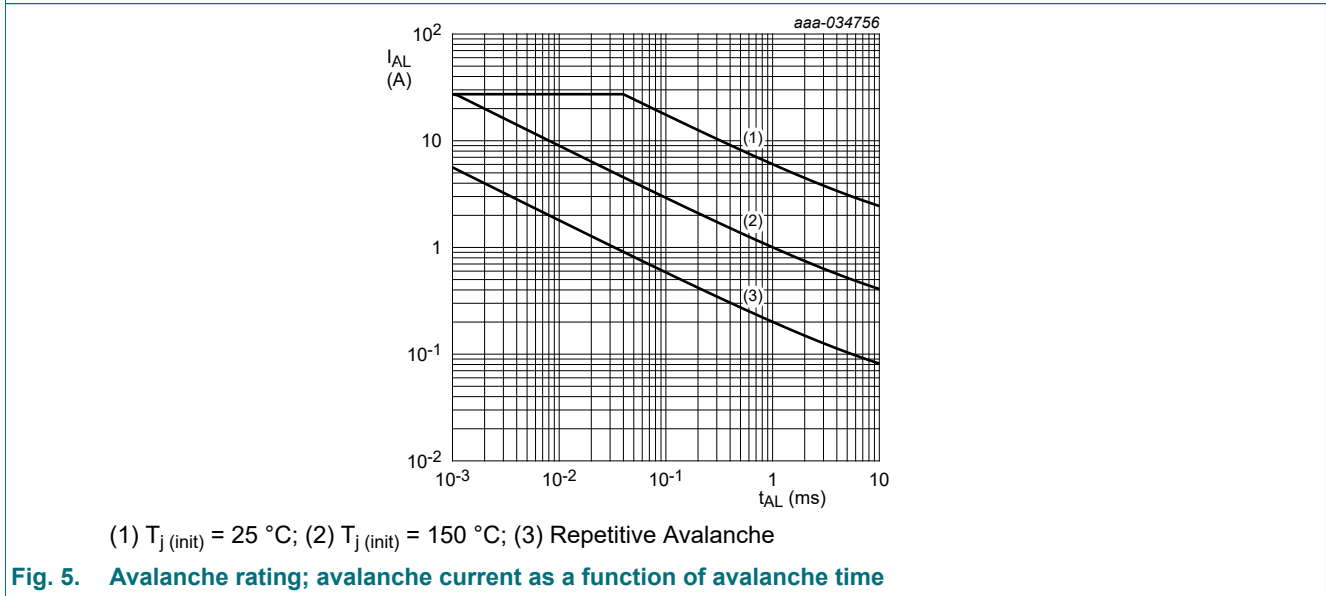
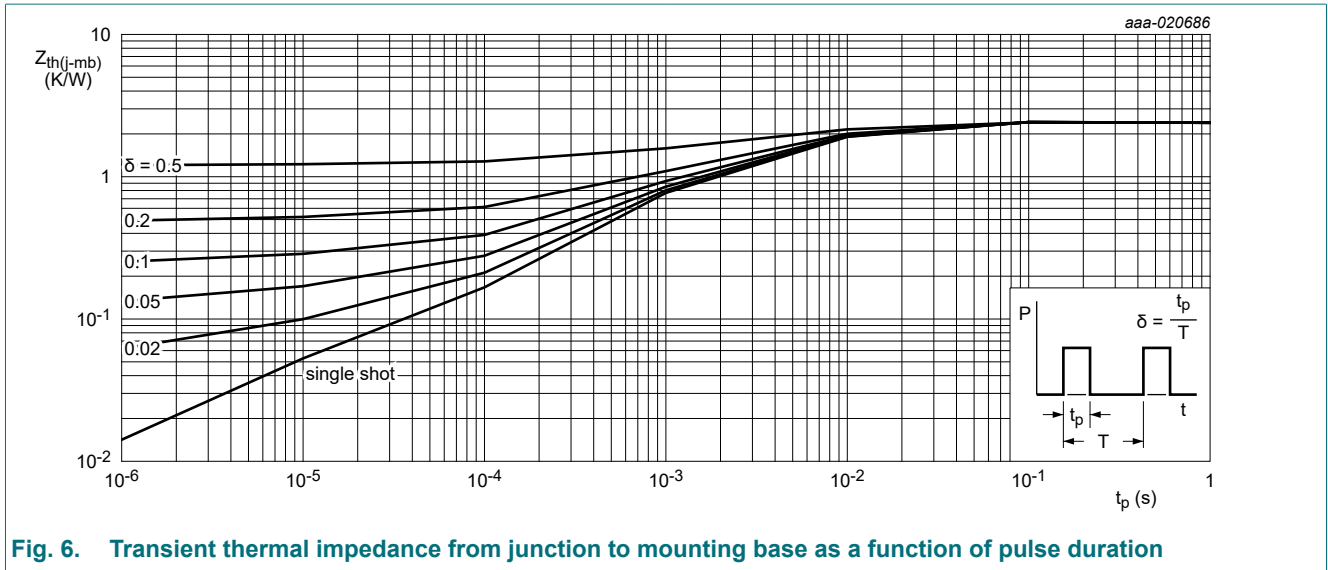


Fig. 5. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6	-	1.91	2.14	K/W



## 10. Characteristics

Table 7. Characteristics

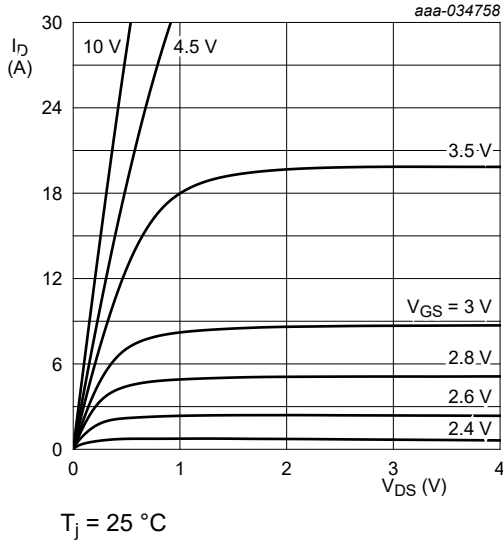
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	60	66	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 \text{ }^\circ C$	54	62	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	54	61	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C; \text{ Fig. 11}; \text{ Fig. 12}$	1.35	1.82	2.05	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C; \text{ Fig. 12}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C; \text{ Fig. 12}$	-	-	2.45	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 175 \text{ }^\circ C$	-	-4.3	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	0.005	1	$\mu A$
		$V_{DS} = 16 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	0.68	10	$\mu A$
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ C$	-	20.7	500	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA

## Single N-channel 60 V, 21 mOhm logic level MOSFET in LPAK33 using Enhanced SOA technology

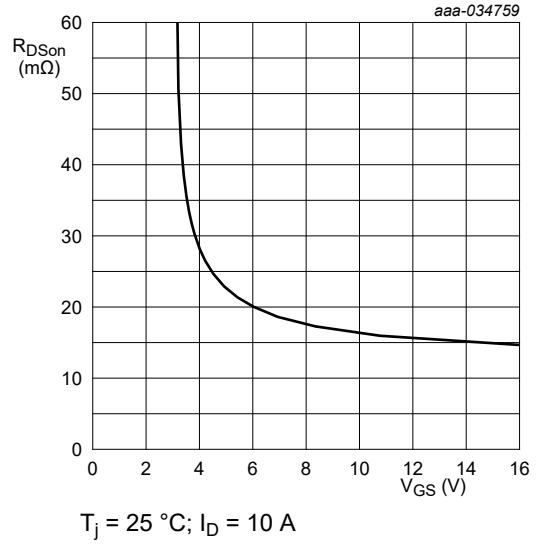
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 13</a>	11.6	16.5	20.6	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 105 °C; <a href="#">Fig. 14</a>	17.8	25.5	33.1	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 125 °C; <a href="#">Fig. 14</a>	19.7	28.1	36.5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 175 °C; <a href="#">Fig. 14</a>	24.7	35.2	45.8	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 13</a>	17.3	24.7	30.9	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 105 °C; <a href="#">Fig. 14</a>	26.3	37.6	48.8	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 125 °C; <a href="#">Fig. 14</a>	28.9	41.2	53.6	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 175 °C; <a href="#">Fig. 14</a>	35.7	51	66.3	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	1.85	-	Ω
<b>Dynamic characteristics</b>						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 4.5 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a> ; <a href="#">Fig. 16</a>	-	12.8	18	nC
		I <sub>D</sub> = 10 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a> ; <a href="#">Fig. 16</a>	-	26.1	36.6	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 5 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a> ; <a href="#">Fig. 16</a>	-	3.7	5.5	nC
Q <sub>GD</sub>	gate-drain charge		-	6	11.9	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 17</a>	-	1334	1774	pF
C <sub>oss</sub>	output capacitance		-	135	162	pF
C <sub>rss</sub>	reverse transfer capacitance		-	79	108	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 48 V; R <sub>L</sub> = 5 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C	-	8.3	-	ns
t <sub>r</sub>	rise time		-	17.7	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	16.5	-	ns
t <sub>f</sub>	fall time		-	12.9	-	ns
g <sub>fs</sub>	transfer conductance		V <sub>DS</sub> = 8 V; I <sub>D</sub> = 10 A	-	24	-
<b>Source-drain diode</b>						
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 10 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 18</a>	-	0.83	1	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 10 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 19</a>	-	26.3	-	ns
Q <sub>r</sub>	recovered charge		[1]	28.5	-	nC

[1] includes capacitive recovery

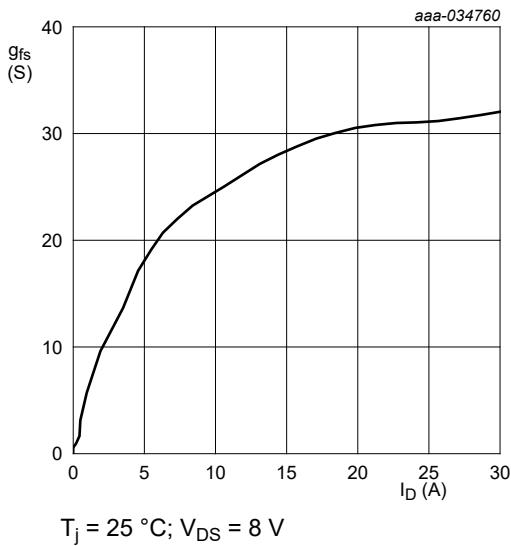
Single N-channel 60 V, 21 mOhm logic level MOSFET in LPAK33 using Enhanced SOA technology



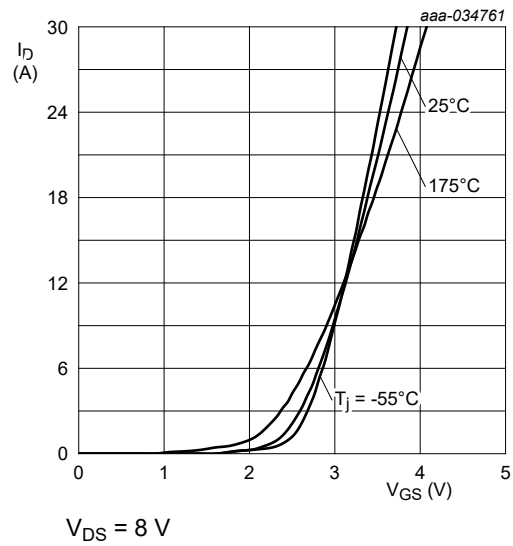
**Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values**



**Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values**

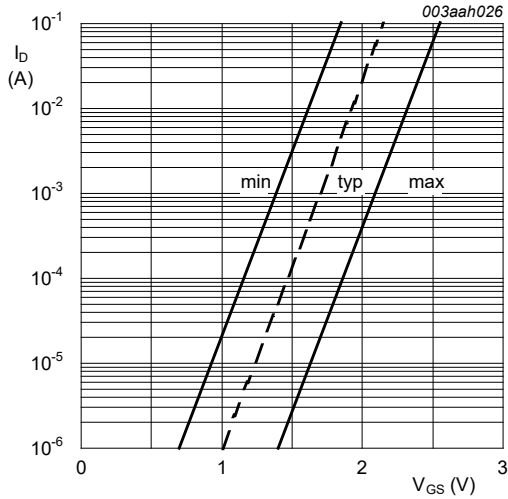


**Fig. 9. Forward transconductance as a function of drain current; typical values**



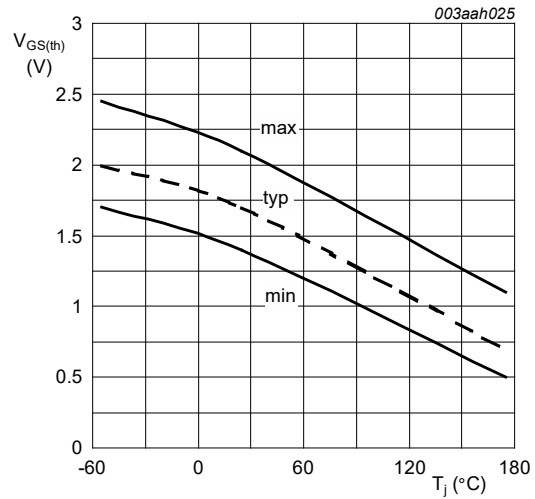
**Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values**

Single N-channel 60 V, 21 mOhm logic level MOSFET in LFPAK33 using Enhanced SOA technology



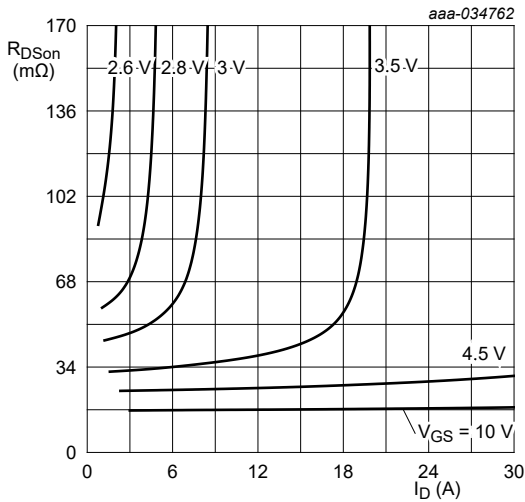
$T_j = 25\text{ }^\circ\text{C}$ ;  $V_{DS} = 5\text{ V}$

**Fig. 11. Sub-threshold drain current as a function of gate-source voltage**



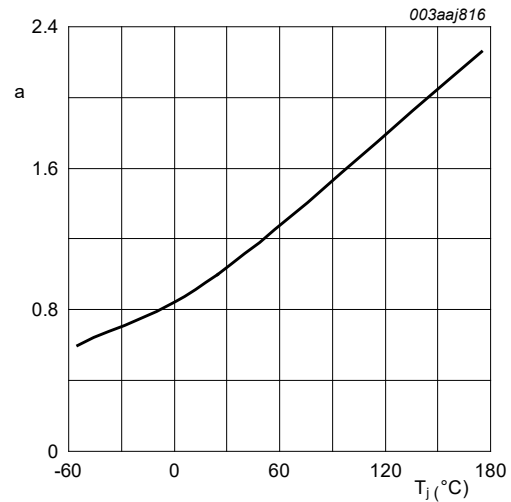
$I_D = 1\text{ mA}$ ;  $V_{DS} = V_{GS}$

**Fig. 12. Gate-source threshold voltage as a function of junction temperature**



$T_j = 25\text{ }^\circ\text{C}$

**Fig. 13. Drain-source on-state resistance as a function of drain current; typical values**



$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

**Fig. 14. Normalized drain-source on-state resistance factor as a function of junction temperature**



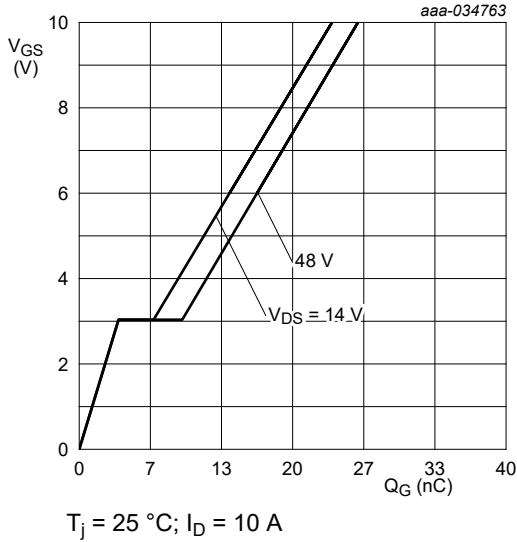


Fig. 15. Gate-source voltage as a function of gate charge; typical values

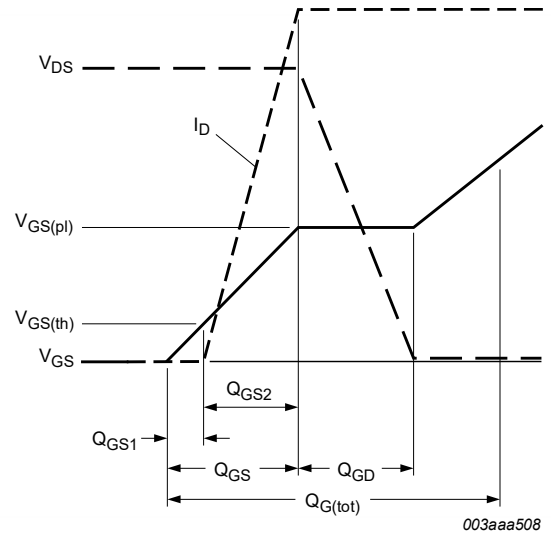


Fig. 16. Gate charge waveform definitions

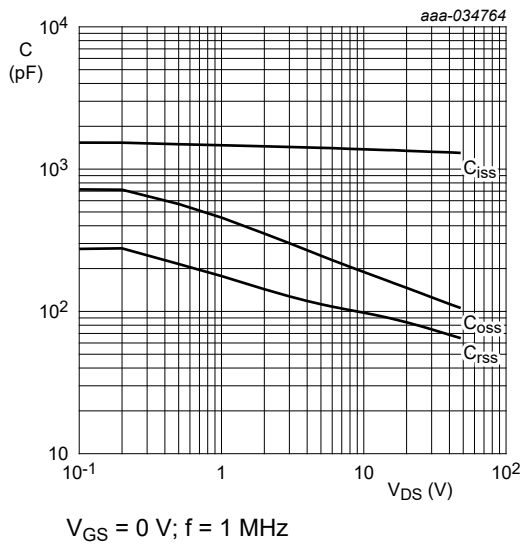


Fig. 17. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

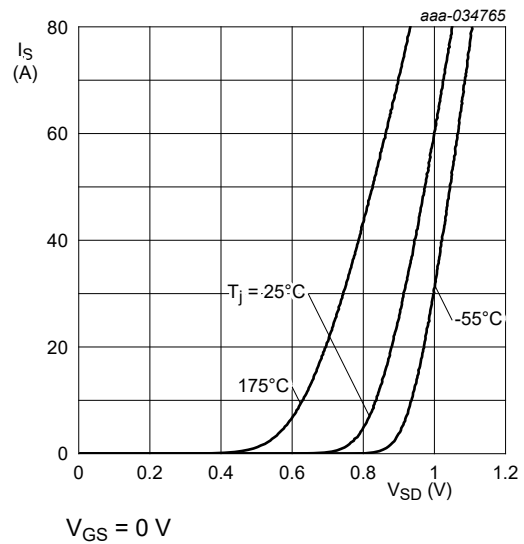


Fig. 18. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

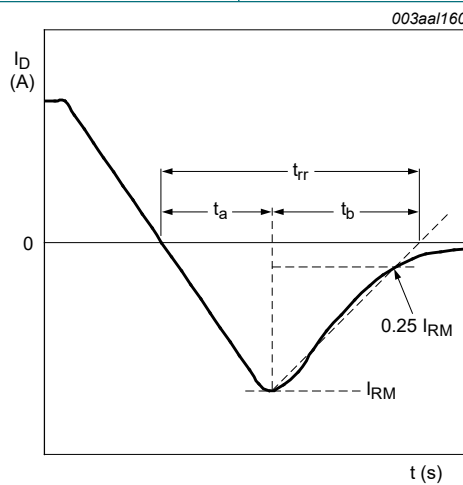


Fig. 19. Reverse recovery timing definition

### 11. Package outline

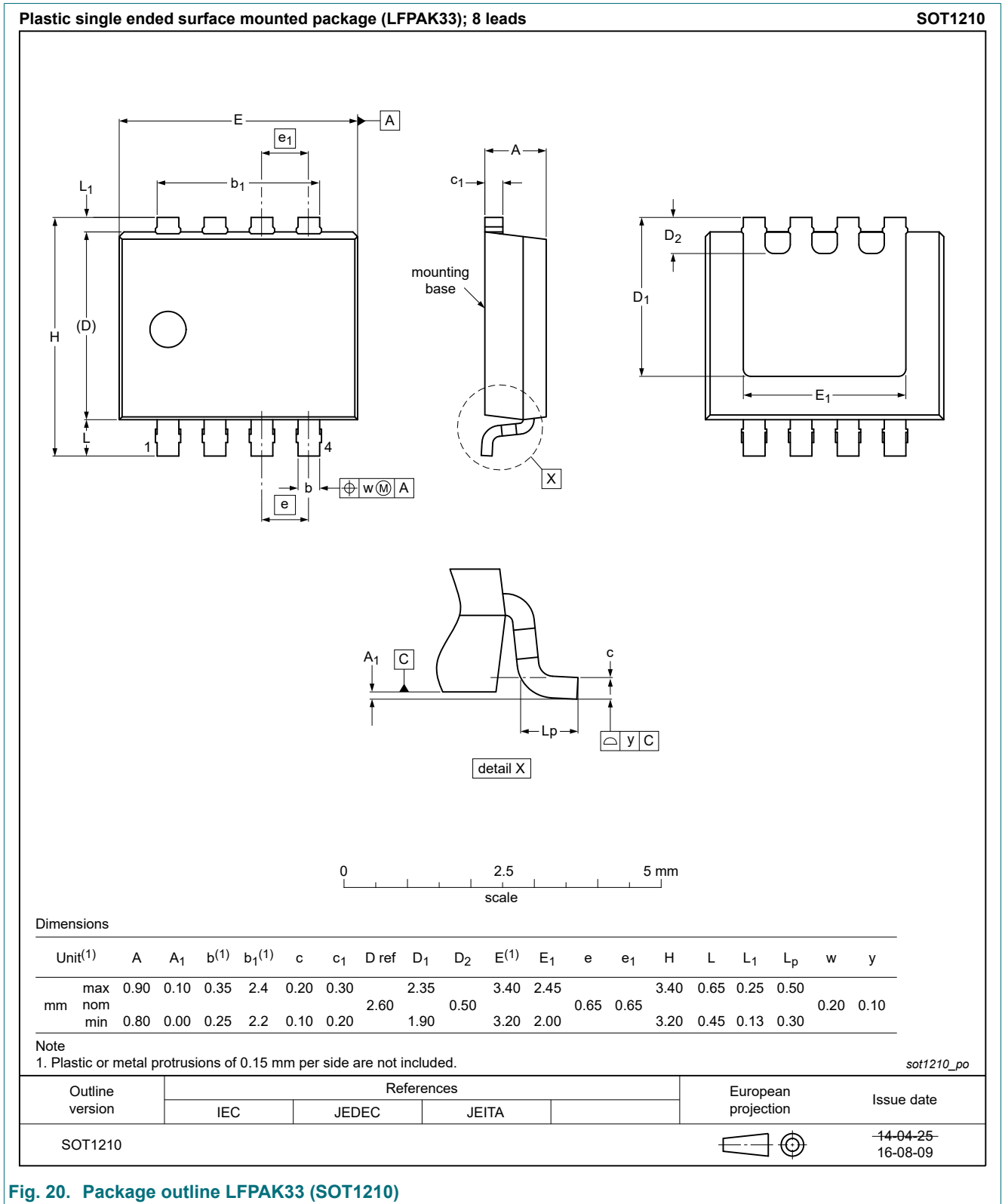


Fig. 20. Package outline LPAK33 (SOT1210)

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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